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U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date appropriate)

FOREIGN PATENT DOCUMENTS

	Document Number	Date	Country	Class	Subclass	Translation Yes No
SM	06-177423	06/24/94	Japan			Abstract
SM	06-196757	07/15/94	Japan			Abstract
SM	09-186363	07/1/97	Japan			Abstract

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

SM	N. Yoshimoto et al., Photoluminescence of InGaN films grown at high temperature by metalorganic vapor phase epitaxy", Appl. Phys. Lett. 59 (18), pp. 2251-2253, October 28, 1991.
SM	S. Nakamura et al., "InGaN-Based Multi-Quantum-Well-Structure Laser Diodes", Jpn. J. Appl. Phys. Vol. 35, Pt. 2, No. 1B, pp. L74-L76, January 15, 1996.
SM	K. Yanashima et al., "Room-Temperature Continuous-Wave Operation of GaN-Based Laser Diodes Grown by Raised-Pressure Metalorganic Chemical Vapor Deposition", Journal of Electronic Materials, Vol. 28, No. 3, pp. 287-289, 1999.

Examiner

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